Ryoichi Suzuki

List of Publications by Year in descending order

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324 papers 5,239 citations

35 h-index 55 g-index

324 all docs

324 docs citations

324 times ranked 3266 citing authors

#	Article	IF	CITATIONS
1	Design and construction of an electron accelerator for a pulsed neutron facility at AIST. Nuclear Instruments & Methods in Physics Research B, 2020, 464, 41-44.	1.4	4
2	Newly constructed compact accelerator-based neutron facility at AIST. EPJ Web of Conferences, 2020, 231, 01002.	0.3	1
3	Gettering of Cu in self-ion irradiated silicon studied by positron annihilation spectroscopy. Japanese Journal of Applied Physics, 2019, 58, 096501.	1.5	3
4	Design of a compact electron accelerator-driven pulsed neutron facility at AIST. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2019, 927, 407-418.	1.6	12
5	Performance evaluation of polyamide TFC membranes: Effects of free volume properties on boron transport. Desalination, 2018, 432, 104-114.	8.2	15
6	Characterization of pore size distribution (PSD) in cellulose triacetate (CTA) and polyamide (PA) thin active layers by positron annihilation lifetime spectroscopy (PALS) and fractional rejection (FR) method. Journal of Membrane Science, 2017, 527, 143-151.	8.2	48
7	Study on Bose-Einstein condensation of positronium. Journal of Physics: Conference Series, 2017, 791, 012007.	0.4	5
8	Detection of re-emission positrons on metal surfaces during slow positron measurements. Journal of Physics: Conference Series, 2017, 791, 012035.	0.4	0
9	Time-resolved positron annihilation spectroscopy study of relaxation dynamics of ion damage in fused quartz. Materials Research Express, 2016, 3, 055201.	1.6	O
10	Hole size distributions in cardo-based polymer membranes deduced from the lifetimes of ortho-positronium. Journal of Physics: Conference Series, 2016, 674, 012017.	0.4	6
11	Development of an X-ray tube for irradiation experiments using a field emission electron gun. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2016, 807, 41-46.	1.6	10
12	Effect of heat treatment on fouling resistance and the rejection of small and neutral solutes by reverse osmosis membranes. Water Science and Technology: Water Supply, 2015, 15, 510-516.	2.1	14
13	Reduction of helium loss from a superconducting accelerating cavity during initial cool-down and cryostat exchange by pre-cooling the re-condensing cryostat. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2015, 776, 83-86.	1.6	0
14	Free Volume Profiles at Polymer–Solid Interfaces Probed by Focused Slow Positron Beam. Macromolecules, 2015, 48, 1493-1498.	4.8	9
15	Stable and high current density electron emission using coniferous carbon nano-structured emitter. Diamond and Related Materials, 2015, 55, 41-44.	3.9	10
16	Probing the internal structure of reverse osmosis membranes by positron annihilation spectroscopy: Gaining more insight into the transport of water and small solutes. Journal of Membrane Science, 2015, 486, 106-118.	8.2	108
17	Digitized detection of gamma-ray signals concentrated in narrow time windows for transient positron annihilation lifetime spectroscopy. Review of Scientific Instruments, 2014, 85, 123110.	1.3	2
18	Development of a compact and fast response detector using an Yb:Lu ₂ O ₃ scintillator for lifetime sensitive positron emission tomography. Journal of Instrumentation, 2014, 9, C05036-C05036.	1,2	1

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19	Vacancy-type defects induced by grinding of Si wafers studied by monoenergetic positron beams. Journal of Applied Physics, 2014, 116, 134501.	2.5	12
20	Structural and defect characterization of Gd-doped GaN films by X-ray diffraction and positron annihilation. Journal of Physics: Conference Series, 2014, 505, 012023.	0.4	0
21	Fabrication and low-power RF test of C-band RF gun. Nuclear Instruments & Methods in Physics Research B, 2014, 331, 27-30.	1.4	1
22	Residual defects in low-dose arsenic-implanted silicon after high-temperature annealing. Nuclear Instruments & Methods in Physics Research B, 2014, 321, 54-58.	1.4	6
23	Structural Defects and Positronium Formation in 40 keV B ⁺ -Implanted Polymethylmethacrylate. Journal of Physical Chemistry B, 2014, 118, 4194-4200.	2.6	20
24	Characterization of polyethylene terephthalate films coated with thin AlxSi1â^'xOy layers using monoenergetic positron beams. Thin Solid Films, 2014, 552, 82-85.	1.8	2
25	(Invited) Point Defect Characterization of Group-III Nitrides by Using Monoenergetic Positron Beams. ECS Transactions, 2014, 61, 19-30.	0.5	14
26	Photon-induced positron annihilation lifetime spectroscopy using an S-band compact electron linac. Radiation Physics and Chemistry, 2014, 95, 30-33.	2.8	4
27	Positron Annihilation in Cardo-Based Polymer Membranes. Journal of Physical Chemistry B, 2014, 118, 6007-6014.	2.6	25
28	Defects in nitride-based semiconductors probed by positron annihilation. Journal of Physics: Conference Series, 2014, 505, 012009.	0.4	1
29	Evaluation of vacancies in positive-tone non-chemically and chemically amplified EUV / EB resists: relationship between free-volume and LER. , 2014, , .		1
30	Rejection of small and uncharged chemicals of emerging concern by reverse osmosis membranes: The role of free volume space within the active skin layer. Separation and Purification Technology, 2013, 116, 426-432.	7.9	44
31	Possible presence of hydrophilic SO ₃ H nanoclusters on the surface of dry ultrathin Nafion® films: a positron annihilation study. Physical Chemistry Chemical Physics, 2013, 15, 1518-1525.	2.8	44
32	Radiation damage in nanocrystalline Ni under irradiation studied using positron annihilation spectroscopy. Journal of Nuclear Materials, 2013, 442, S856-S860.	2.7	8
33	Vacancy-type defects in $InxCalâ^*xN grown on GaN templates probed using monoenergetic positron beams. Journal of Applied Physics, 2013, 114, .$	2.5	15
34	On determining the entrance size of cage-like pores in mesoporous silica films by positron annihilation lifetime spectroscopy. Chemical Physics Letters, 2013, 590, 97-100.	2.6	11
35	Vacancy-type defects introduced by plastic deformation of GaN studied using monoenergetic positron beams. Journal of Applied Physics, $2013,114,.$	2.5	8
36	Development of a sample chamber with humidity control for an atmospheric positron probe microanalyzer. Journal of Physics: Conference Series, 2013, 443, 012090.	0.4	1

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37	Vacancy reactions near the interface between electroplated Cu and barrier metal layers studied by monoenergetic positron beams. Journal of Applied Physics, 2013, 114, 074510.	2.5	5
38	Characterization of Porous Structures in Advanced Low-kFilms with Thin TaN Layers Using Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 2013, 52, 106501.	1.5	9
39	Positron Annihilation Spectroscopy on Nitride-Based Semiconductors. Japanese Journal of Applied Physics, 2013, 52, 08JJ02.	1.5	26
40	In-situ positron lifetime spectroscopy of radiation damage by simultaneous irradiation of slow-positron and ion beams. Journal of Physics: Conference Series, 2013, 443, 012043.	0.4	5
41	Material characterization for advanced Si LSI process technology by means of positron annihilation. Journal of Physics: Conference Series, 2013, 443, 012067.	0.4	1
42	Vacancy profile in reverse osmosis membranes studied by positron annihilation lifetime measurements and molecular dynamics simulations. Journal of Physics: Conference Series, 2013, 443, 012050.	0.4	7
43	Monte Carlo simulations of the extraction of slow positrons into gas through thin SiN windows. Journal of Physics: Conference Series, 2013, 443, 012069.	0.4	1
44	Vacancy-Type Defects Introduced by Gas Cluster Ion-Implantation on Si Studied by Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 2012, 51, 111801.	1.5	2
45	Free volume change of elongated polyethylene films studied using a positron probe microanalyzer. Applied Physics Letters, 2012, 101, 203108.	3.3	9
46	<i>In-situ</i> characterization of free-volume holes in polymer thin films under controlled humidity conditions with an atmospheric positron probe microanalyzer. Applied Physics Letters, 2012, 101, .	3.3	25
47	Vacancy clustering and its dissociation process in electroless deposited copper films studied by monoenergetic positron beams. Journal of Applied Physics, 2012, 111, 104506.	2.5	11
48	Tailoring the Chain Packing in Ultrathin Polyelectrolyte Films Formed by Sequential Adsorption: Nanoscale Probing by Positron Annihilation Spectroscopy. Journal of the American Chemical Society, 2012, 134, 19808-19819.	13.7	22
49	Development of a Slow Positron Beam System for in-situ Lifetime Measurements During Ion Beam Irradiation. Physics Procedia, 2012, 35, 111-116.	1.2	6
50	Variable-energy Positron Study of Nanopore Structure in Hydrocarbon–Siliconoxide Hybrid PECVD Films. Physics Procedia, 2012, 35, 140-144.	1.2	8
51	Temperature Dependence of Defects in Hydrogen-Implanted Silicon Characterized by Positron and Ion-Beam Analyses. Physics Procedia, 2012, 35, 151-156.	1.2	1
52	Native cation vacancies in Si-doped AlGaN studied by monoenergetic positron beams. Journal of Applied Physics, 2012, 111, .	2.5	53
53	Role of pore morphology in positronium diffusion in mesoporous silica thin films and in positronium emission from the surfaces. Physical Review B, 2012, 86, .	3.2	40
54	Subnanoscopic Holes in Composite Membranes for Desalination Elucidated by Energy-Tunable Positron Annihilation. Kobunshi Ronbunshu, 2012, 69, 443-447.	0.2	6

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55	Vacancy-Type Defects Introduced by Gas Cluster Ion-Implantation on Si Studied by Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 2012, 51, 111801.	1.5	3
56	Correlation Study between Free-Volume Holes and Molecular Separations of Composite Membranes for Reverse Osmosis Processes by Means of Variable-Energy Positron Annihilation Techniques. Journal of Physical Chemistry C, 2011, 115, 18055-18060.	3.1	69
57	Pore Size Determination of TEMPO-Oxidized Cellulose Nanofibril Films by Positron Annihilation Lifetime Spectroscopy. Biomacromolecules, 2011, 12, 4057-4062.	5.4	105
58	Simulations of slow positron production using a low-energy electron accelerator. Review of Scientific Instruments, 2011, 82, 063302.	1.3	13
59	Development of a dedicated superconducting accelerator for positron production. Journal of Physics: Conference Series, 2011, 262, 012043.	0.4	6
60	Application of positron annihilation technique to front and backend processes for modern LSI devices. Journal of Physics: Conference Series, 2011, 262, 012061.	0.4	0
61	Imaging of the distribution of average positron lifetimes by using a positron probe microanalyzer. Journal of Physics: Conference Series, 2011, 262, 012044.	0.4	8
62	Vacancy evolution in Ni during irradiation at high temperatures studied by in situ positron annihilation spectroscopy. Journal of Physics: Conference Series, 2011, 262, 012060.	0.4	5
63	Defect profiles in ion-irradiated metal samples by slow positron beams in comparison with simulation profiles. Journal of Physics: Conference Series, 2011, 262, 012029.	0.4	9
64	Low energy positron annihilation study of composite reverse osmosis membranes. Journal of Physics: Conference Series, 2011, 262, 012013.	0.4	4
65	Slow Positron Beam Apparatus for Surface and Subsurface Analysis of Samples in Air. Applied Physics Express, 2011, 4, 066701.	2.4	14
66	Depth profiling of defects in ion-implanted Ni and Fe by positron annihilation measurements. Surface and Coatings Technology, 2011, 206, 834-836.	4.8	7
67	Highâ€rate crystallization of polycarbonate in spincast thin film. Journal of Polymer Science, Part B: Polymer Physics, 2010, 48, 2148-2153.	2.1	6
68	Mesoporous silica films with varying porous volume fraction: Direct correlation between ortho-positronium annihilation decay and escape yield into vacuum. Applied Physics Letters, 2009, 95, 124103.	3.3	20
69	Rapid three-dimensional imaging of defect distributions using a high-intensity positron microbeam. Applied Physics Letters, 2009, 94, 194104.	3.3	43
70	Characterization of Low-k/Cu Damascene Structures Using Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 2009, 48, 120222.	1.5	10
71	A positron annihilation lifetime measurement system with an intense positron microbeam. Radiation Physics and Chemistry, 2009, 78, 1096-1098.	2.8	21
72	Point defects in group-III nitride semiconductors studied by positron annihilation. Journal of Crystal Growth, 2009, 311, 3075-3079.	1.5	51

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73	Free volume behavior in spincast thin film of polystyrene by energy variable positron annihilation lifetime spectroscopy. Polymer, 2009, 50, 3343-3346.	3.8	34
74	A variable energy positron annihilation lifetime spectroscopy study of physical aging in thin glassy polymer films. Polymer, 2009, 50, 6149-6156.	3.8	97
75	Characterization of Low-k SiOCH Layers in fine-pitch Cu-damascene interconnects by monoenergetic positron beams., 2009,,.		0
76	Orthopositronium annihilation and emission in mesostructured thin silica and silicalite-1 films. Applied Surface Science, 2008, 255, 187-190.	6.1	14
77	Application of positron beams to the study of positronium-forming solids. Applied Surface Science, 2008, 255, 174-178.	6.1	22
78	Evolution of pores in mesoporous silica films: Porogen loading effect. Applied Surface Science, 2008, 255, 183-186.	6.1	14
79	Study of mirror degradation in short-wavelength FELs and recent FEL application experiments on the storage ring NIJI-IV. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2008, 593, 17-20.	1.6	0
80	Annihilation characteristics of positrons in free-standing thin metal and polymer films. Nuclear Instruments & Methods in Physics Research B, 2008, 266, 750-754.	1.4	1
81	Effect of UV anneal on plasma CVD low-k film. Journal of Non-Crystalline Solids, 2008, 354, 2973-2982.	3.1	22
82	Positron Trapping Sites Originating from Oxide Interfaces on 4H-SiC C(000ar1)- and Si(0001)-Faces. Japanese Journal of Applied Physics, 2008, 47, 8391-8393.	1.5	1
83	Temperature-dependent growth and transient state of hydrogen-induced nanocavities in silicon. Journal of Applied Physics, 2008, 104, .	2.5	6
84	Positronium reemission yield from mesostructured silica films. Applied Physics Letters, 2008, 92, .	3.3	70
85	Brightness enhancement method for a high-intensity positron beam produced by an electron accelerator. Journal of Applied Physics, 2008, 103, .	2.5	53
86	Impact of Residual Impurities on Annealing Properties of Vacancies in Electroplated Cu Studied Using Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 2007, 46, L483-L485.	1.5	9
87	Defects in Electroplated Cu and Their Impact on Stress Migration Reliability Studied using Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 2007, 46, 1938-1941.	1.5	8
88	Characterization of Metal/High-kStructures Using Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 2007, 46, 3214-3218.	1.5	9
89	Evidence for pore surface dependent positronium thermalization in mesoporous silica/hybrid silica films. Physical Review B, 2007, 75, .	3.2	49
90	Annealing properties of open volumes in strained SiN films studied by monoenergetic positron beams. Journal of Applied Physics, 2007, 102, 064513.	2.5	5

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91	Annealing properties of vacancy-type defects in ion-implanted GaN studied by monoenergetic positron beams. Journal of Applied Physics, 2007, 102, 084505.	2.5	38
92	Vacancy-fluorine complexes and their impact on the properties of metal-oxide transistors with high-k gate dielectrics studied using monoenergetic positron beams. Journal of Applied Physics, 2007, 102, 054511.	2.5	5
93	Positronium annihilation and pore surface chemistry in mesoporous silica films. Applied Physics Letters, 2007, 91, .	3.3	34
94	Free-Volume Depth Profile of Polymeric Membranes Studied by Positron Annihilation Spectroscopy:  Layer Structure from Interfacial Polymerization. Macromolecules, 2007, 40, 7542-7557.	4.8	249
95	Cu / Barrier Metal Stack Film Characterization for Reliability Estimation. , 2007, , .		1
96	Tunable pores in mesoporous silica films studied using a pulsed slow positron beam. Radiation Physics and Chemistry, 2007, 76, 204-208.	2.8	23
97	Variable-energy positron annihilation study of subnanopores in SiOCH-based PECVD films. Radiation Physics and Chemistry, 2007, 76, 213-216.	2.8	20
98	Positronium formation in fused quartz: Experimental evidence of delayed formation. Radiation Physics and Chemistry, 2007, 76, 330-332.	2.8	5
99	Study of highâ€∢i>k gate dielectrics by means of positron annihilation. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 3599-3604.	0.8	0
100	Design of a liquidless superconducting accelerator for positron annihilation lifetime spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 4023-4027.	0.8	3
101	Development of a Naâ€22 based pulsed slow positron beam for depthâ€selective PALS. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 4020-4022.	0.8	11
102	Studying conductive polymer coating (BAMâ€PPV) using positron annihilation spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 3789-3792.	0.8	0
103	Study of mesoporous silica films by positron annihilation based on a slow positron beam: Effects of preparation conditions on pore size and open porosity. Chemical Physics, 2007, 331, 213-218.	1.9	19
104	Free-volume distribution and glass transition of nano-scale polymeric films. Radiation Physics and Chemistry, 2007, 76, 172-179.	2.8	29
105	Porogen Approach for the Fabrication of Plasma-Polymerized Nanoporous Polysiloxane Films. Journal of Physical Chemistry B, 2006, 110, 20172-20176.	2.6	31
106	Slow positron beam study of corrosion-related defects in pure iron. Applied Surface Science, 2006, 252, 3274-3277.	6.1	18
107	Positron annihilation studies of mesoporous silica films using a slow positron beam. Applied Surface Science, 2006, 252, 3221-3227.	6.1	7
108	Ageing-induced enhancement of open porosity of mesoporous silica films studied by positron annihilation spectroscopy. Physics Letters, Section A: General, Atomic and Solid State Physics, 2006, 355, 73-76.	2.1	12

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109	Defect layer in SiO2–SiC interface proved by a slow positron beam. Physica B: Condensed Matter, 2006, 376-377, 354-357.	2.7	2
110	Impact of nitridation on open volumes in HfSiOx studied using monoenergetic positron beams. Applied Physics Letters, 2006, 88, 171912.	3.3	10
111	Vacancy-impurity complexes in polycrystalline Si used as gate electrodes of HfSiON-based metal-oxide-semiconductors probed using monoenergetic positron beams. Journal of Applied Physics, 2006, 100, 034509.	2.5	7
112	Characterization of HfSiON gate dielectrics using monoenergetic positron beams. Journal of Applied Physics, 2006, 99, 054507.	2.5	22
113	Open volumes in SiN films for strained Si transistors probed using monoenergetic positron beams. Applied Physics Letters, 2006, 88, 252107.	3.3	4
114	Structure of SiO2 â° 4 Hâ° SiCinterface probed by positron annihilation spectroscopy. Physical Review B, 2006, 73, .	3.2	20
115	Structural defects in SiO2/SiC interface probed by a slow positron beam. Applied Surface Science, 2005, 244, 322-325.	6.1	14
116	Fabrication of Microparticle Layer by Annealing Microparticle/Polymer Composite. Japanese Journal of Applied Physics, 2005, 44, L268-L270.	1.5	0
117	Reemission of Positrons from Mesh and Powder Moderators. Japanese Journal of Applied Physics, 2005, 44, 6283-6286.	1.5	3
118	Low-kSiOCH Film Deposited by Plasma-Enhanced Chemical Vapor Deposition Using Hexamethyldisiloxane and Water Vapor. Japanese Journal of Applied Physics, 2005, 44, 3879-3884.	1.5	15
119	Interaction of nitrogen with vacancy defects in N+-implanted ZnO studied using a slow positron beam. Applied Physics Letters, 2005, 87, 091910.	3.3	29
120	Annealing properties of open volumes in HfSiOx and HfAlOx gate dielectrics studied using monoenergetic positron beams. Journal of Applied Physics, 2005, 98, 023506.	2.5	20
121	Vacancy-type defects in Si-doped InN grown by plasma-assisted molecular-beam epitaxy probed using monoenergetic positron beams. Journal of Applied Physics, 2005, 97, 043514.	2.5	14
122	Mechanism of enhanced positronium formation in low-temperature polymers. Journal of Chemical Physics, 2005, 122, 214907.	3.0	30
123	Vacancy-type defects in strained-Si layers deposited on SiGeâ [*] -Si structures probed by using monoenergetic positron beams. Journal of Applied Physics, 2005, 97, 023532.	2.5	5
124	Defects introduced into electroplated Cu films during room-temperature recrystallization probed by a monoenergetic positron beam. Journal of Applied Physics, 2005, 98, 043504.	2.5	24
125	Microvoid formation in hydrogen-implantedZnOprobed by a slow positron beam. Physical Review B, 2005, 71, .	3.2	89
126	Production and recovery of defects in phosphorus-implanted ZnO. Journal of Applied Physics, 2005, 97, 013528.	2.5	128

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127	Characterization of Hf0.3Al0.70xFabricated by Atomic-Layer-Deposition Technique Using Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 2004, 43, 7848-7852.	1.5	7
128	Properties of Low-kCu Barrier SiOCNH Film Deposited by Plasma-Enhanced Chemical Vapor Deposition using Hexamethyldisiloxane and Ammonia Gases. Japanese Journal of Applied Physics, 2004, 43, 750-756.	1.5	8
129	Characterizing Metal-Oxide Semiconductor Structures Consisting of HfSiOxas Gate Dielectrics using Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 2004, 43, 1254-1259.	1.5	7
130	Influence of defect-impurity complexes on slow positron yield of a tungsten moderator: Positron annihilation, Auger, and SIMS study. Physical Review B, 2004, 69, .	3.2	5
131	Evolution of voids inAl+-implanted ZnO probed by a slow positron beam. Physical Review B, 2004, 69, .	3.2	93
132	Identification of vacancy–oxygen complexes in oxygen-implanted silicon probed with slow positrons. Journal of Applied Physics, 2004, 95, 3404-3410.	2.5	8
133	The Depth Profile of Free Volume in Drug Delivery Polymers Studied by Positron Annihilation Spectroscopy. Materials Science Forum, 2004, 445-446, 319-321.	0.3	3
134	Positronium Annihilation Lifetime Spectroscopy of Porous Low-k Films with Periodic Pore Structures. Materials Science Forum, 2004, 445-446, 334-336.	0.3	4
135	Estimation of Ni / Polyethylene Bilayer by Slow Positron Beam. Materials Science Forum, 2004, 445-446, 42-44.	0.3	1
136	Positronium Time-Of-Flight Measurements of Porous Silsesquioxane Films. Materials Science Forum, 2004, 445-446, 361-363.	0.3	2
137	Positron Annihilation Methods by Î ³ -Rays Produced in Laser-Induced Compton-Backscattering. Materials Science Forum, 2004, 445-446, 474-476.	0.3	3
138	Depth Profiling of Ultra-Thin Polymer Films on Substrates Studied by Positron Annihilation Spectroscopy. Materials Science Forum, 2004, 445-446, 367-369.	0.3	4
139	Positron and Positronium Annihilation in Low-Dielectric-Constant Films Studied by a Pulsed Positron Beam. Materials Science Forum, 2004, 445-446, 224-228.	0.3	7
140	Positron Annihilation Study on Hydrogen-Induced Defects in AISI 304 Stainless Steel. Materials Science Forum, 2004, 445-446, 213-215.	0.3	3
141	Ion-Implantation Induced Defects in ZnO Studied by a Slow Positron Beam. Materials Science Forum, 2004, 445-446, 57-59.	0.3	3
142	Copper Barrier Properties of Low Dielectric Constant SiOCNH Film Deposited by Plasma-Enhanced CVD. Journal of the Electrochemical Society, 2004, 151, C56.	2.9	11
143	Depth Dependence of Defects in Ion-Implanted Si Probed by a Positron Beam. Materials Science Forum, 2004, 445-446, 78-80.	0.3	2
144	Durability and Free Volume in Polymeric Coatings Studied by Positron Annihilation Spectroscopy. Materials Science Forum, 2004, 445-446, 274-276.	0.3	14

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145	Positron Beam Study of Defects Induced in Ar-Implanted Si. Materials Science Forum, 2004, 445-446, 150-152.	0.3	4
146	Characterization of photoresists for ArF-excimer laser lithography using monoenergetic positron beams. Journal of Polymer Science, Part B: Polymer Physics, 2004, 42, 341-346.	2.1	0
147	Characterization of free volume and density gradients of polystyrene surfaces by low-energy positron lifetime measurements. Polymer, 2004, 45, 4533-4539.	3.8	43
148	Free Volume and Density Gradients of Amorphous Polymer Surfaces As Determined by Use of a Pulsed Low-Energy Positron Lifetime Beam and PVT Data. Macromolecules, 2004, 37, 4201-4210.	4.8	28
149	Positron emission tomography imaging of musculoskeletal tumors in the shoulder girdle. Journal of Shoulder and Elbow Surgery, 2004, 13, 635-647.	2.6	10
150	Nanopore Structure of Sputtered Silica Thin Films Probed by Spectroscopic Ellipsometry and Variable-Energy Positron Annihilation. Journal of the Ceramic Society of Japan, 2004, 112, 338-341.	1.3	3
151	A positron beam study of vacancy–impurity complexes in inert gas ion-implanted silicon. Physica B: Condensed Matter, 2003, 340-342, 724-728.	2.7	6
152	Defects introduced into SrTiO3 by auto-feeding epitaxy studied using positron annihilation technique. Materials Science in Semiconductor Processing, 2003, 6, 367-369.	4.0	2
153	Positron and positronium annihilation in silica-based thin films studied by a pulsed positron beam. Radiation Physics and Chemistry, 2003, 68, 339-343.	2.8	11
154	Positron studies of polymeric coatings. Radiation Physics and Chemistry, 2003, 68, 395-402.	2.8	17
155	Mesoporous low-k hydrogen-silsesquioxane films characterized by positron annihilation and other techniques. Radiation Physics and Chemistry, 2003, 68, 435-437.	2.8	12
156	Surface and interfacial effect on polymer glass transition temperature studied by positron annihilation. Radiation Physics and Chemistry, 2003, 68, 535-539.	2.8	8
157	Salt weathering effect of polymer coatings studied by positron annihilation spectroscopy. Radiation Physics and Chemistry, 2003, 68, 581-587.	2.8	6
158	Depth Profile of Free Volume in a Mixture and Copolymers of Poly(N-vinyl-pyrrolidone) and Poly(ethylene glycol) Studied by Positron Annihilation Spectroscopy. Biomacromolecules, 2003, 4, 1856-1864.	5.4	45
159	Helium ion implantation-induced defects in silicon probed with variable-energy positrons. Physical Review B, 2003, 68, .	3.2	11
160	Properties of Low-k Copper Barrier SiOCH Film Deposited by PECVD Using Hexamethyldisiloxane and N[sub 2]O. Journal of the Electrochemical Society, 2003, 150, F83.	2.9	28
161	Characterization of Porous Silicate Low-k Films by Ellipsometric Porosimetry and Variable-energy Positron Annihilation Spectroscopy. Materials Research Society Symposia Proceedings, 2003, 788, 8191.	0.1	3
162	Positronium time-of-flight measurements of porous low-k films. Applied Physics Letters, 2003, 83, 4966-4968.	3.3	26

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163	Hydrogen-terminated defects in ion-implanted silicon probed by monoenergetic positron beams. Journal of Applied Physics, 2003, 93, 3228-3233.	2.5	22
164	Quantum Antidot Formation and Correlation to Optical Shift of Gold Nanoparticles Embedded in MgO. Physical Review Letters, 2002, 88, 175502.	7.8	29
165	Characterization of Mg doped GaN by positron annihilation spectroscopy. Journal of Applied Physics, 2002, 92, 1898-1901.	2.5	13
166	Vacancy-type defects in BaTiO3/SrTiO3 structures probed by monoenergetic positron beams. Journal of Applied Physics, 2002, 91, 5307-5312.	2.5	33
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